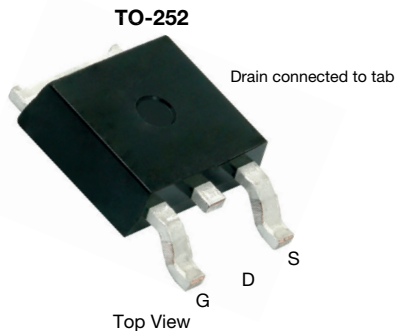


N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A) ^c	Q _g (TYP.)
100	0.0089 at V _{GS} = 10 V	50	33 nC
	0.0093 at V _{GS} = 7.5 V	50	


Ordering Information:

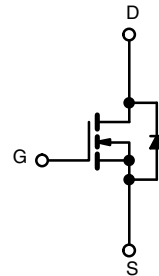
SUD70090E-GE3 (lead (Pb)-free and halogen-free)

FEATURES

- ThunderFET® power MOSFET
- Maximum 175 °C junction temperature
- Q_{gd} / Q_{gs} ratio < 1 optimizes switching characteristics
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT
HALOGEN
FREE
APPLICATIONS

- DC/DC converter
- Power tools
- Motor drive switch
- DC/AC inverter
- Battery management



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage		V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	I _D	50 ^c	A
	T _C = 70 °C		50 ^c	
Pulsed Drain Current (t = 100 μs)		I _{DM}	120	
Avalanche Current		I _{AS}	40	
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	80	mJ
Maximum Power Dissipation ^a	T _C = 25 °C	P _D	125	W
	T _C = 70 °C ^b		87.5	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) ^b		R _{thJA}	40	°C/W
Junction-to-Case (Drain)		R _{thJC}	1.2	

Notes

- Duty cycle ≤ 1 %.
- When mounted on 1" square PCB (FR4 material).
- Package limited.

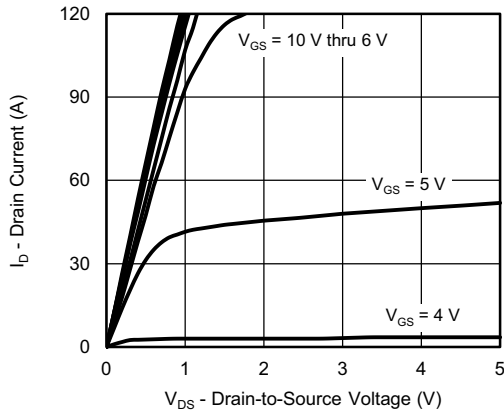
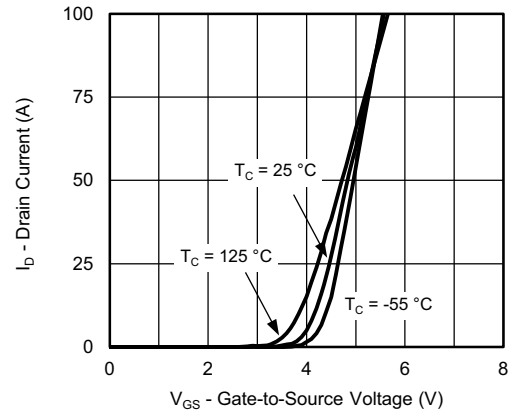
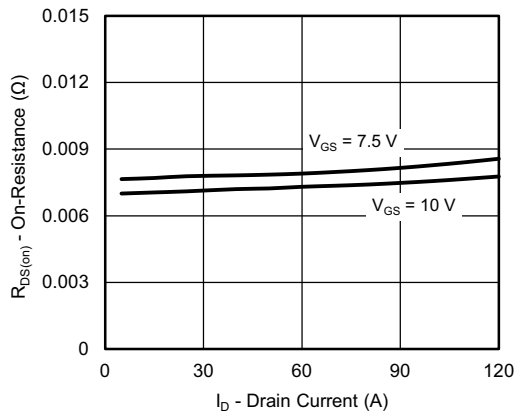
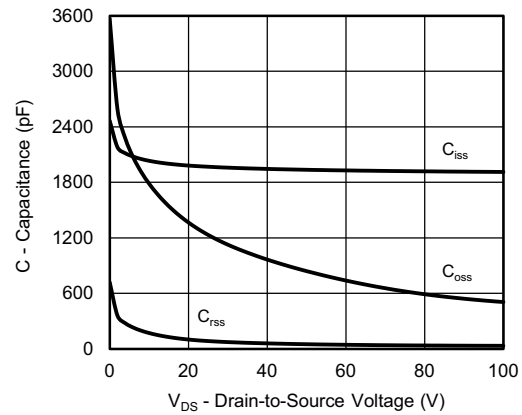
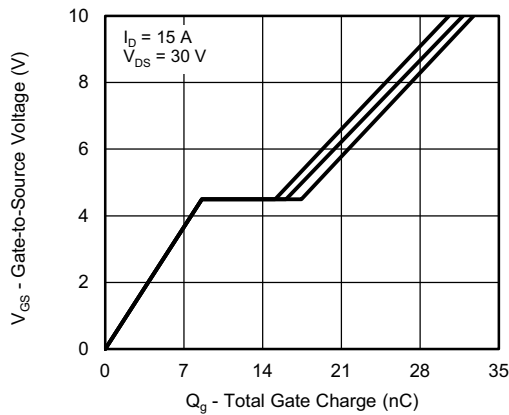
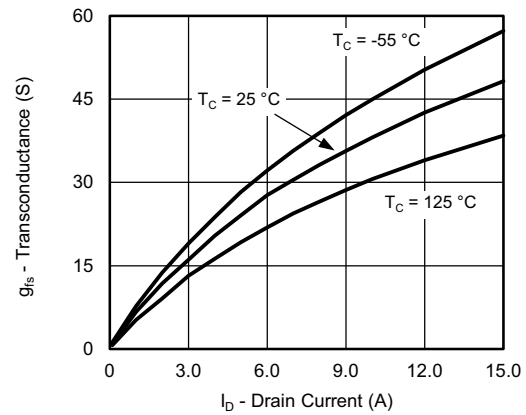


SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	100	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2	-	4	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	± 250	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 125 °C	-	-	150	
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 175 °C	-	-	5	mA
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = 10 V	50	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A	-	0.0074	0.0089	Ω
		V _{GS} = 7.5 V, I _D = 15 A	-	0.0077	0.0093	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 10 A	-	38	-	S
Dynamic ^b						
Input Capacitance	C _{ISS}	V _{GS} = 0 V, V _{DS} = 50 V, f = 1 MHz	-	1950	-	pF
Output Capacitance	C _{OSS}		-	845	-	
Reverse Transfer Capacitance	C _{RSS}		-	54	-	
Total Gate Charge ^c	Q _g	V _{DS} = 50 V, V _{GS} = 10 V, I _D = 20 A	-	33	50	nC
Gate-Source Charge ^c	Q _{gs}		-	8.8	-	
Gate-Drain Charge ^c	Q _{gd}		-	7.5	-	
Gate Resistance	R _g	f = 1 MHz	0.7	3.5	7	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 50 V, R _L = 5 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω	-	15	30	ns
Rise Time ^c	t _r		-	27	54	
Turn-Off Delay Time ^c	t _{d(off)}		-	36	72	
Fall Time ^c	t _f		-	45	90	
Drain-Source Body Diode Ratings and Characteristics ^b (T_C = 25 °C)						
Pulsed Current (t = 100 μs)	I _{SM}		-	-	120	A
Forward Voltage ^a	V _{SD}	I _F = 10 A, V _{GS} = 0 V	-	0.8	1.5	V
Reverse Recovery Time	t _{rr}	I _F = -10 A, di/dt = 100 A/μs	-	77	116	ns
Peak Reverse Recovery Charge	I _{RM(REC)}		-	4.2	6.3	A
Reverse Recovery Charge	Q _{rr}		-	145	365	nC

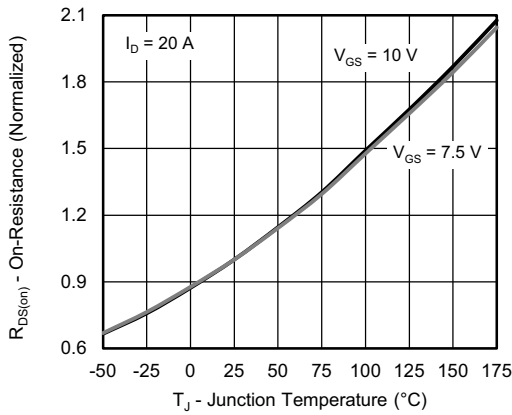
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

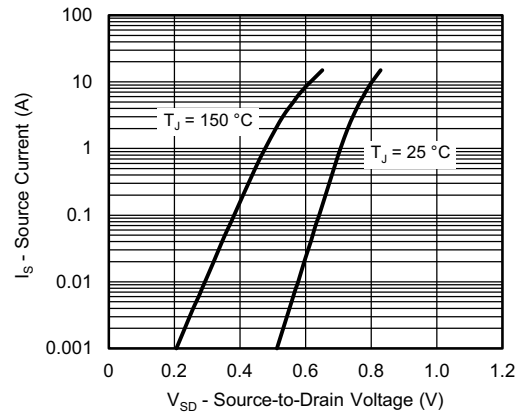
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Capacitance

Gate Charge

Transconductance

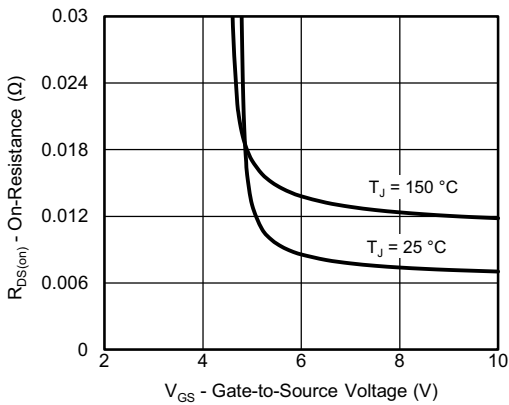
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



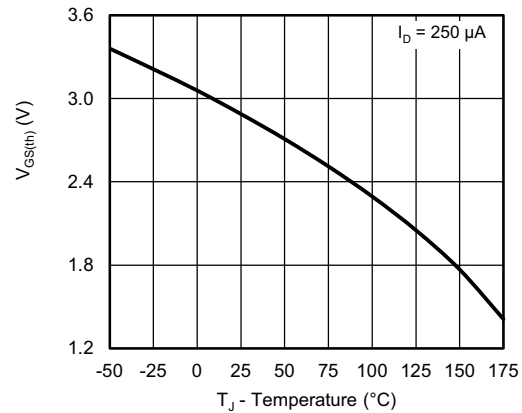
On-Resistance vs. Junction Temperature



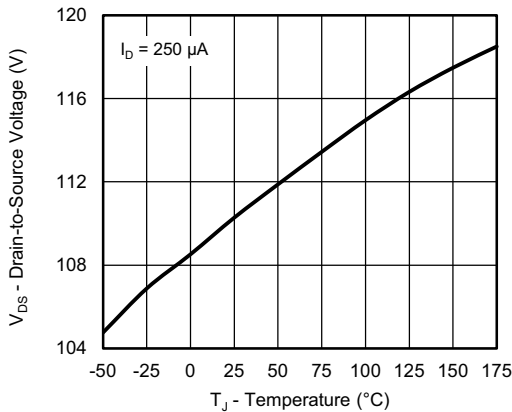
Source Drain Diode Forward Voltage



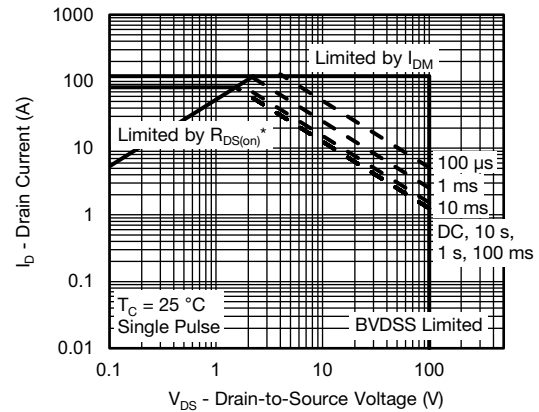
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



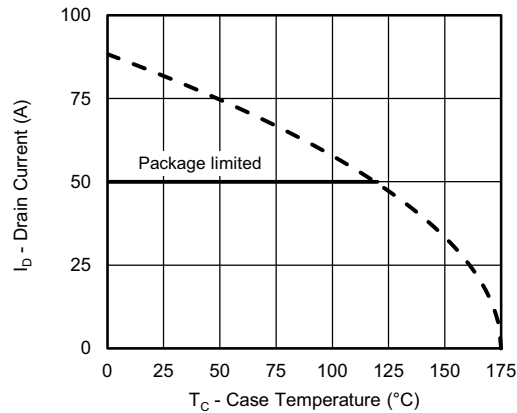
Drain Source Voltage vs. Junction Temperature



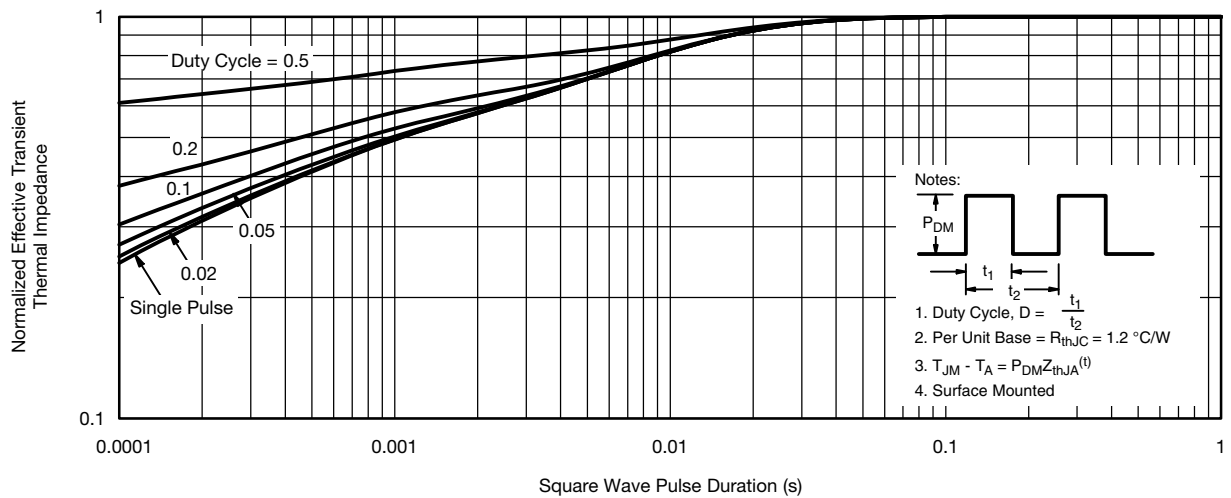
Safe Operating Area



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Current De-Rating



Normalized Thermal Transient Impedance, Junction-to-Case

Note

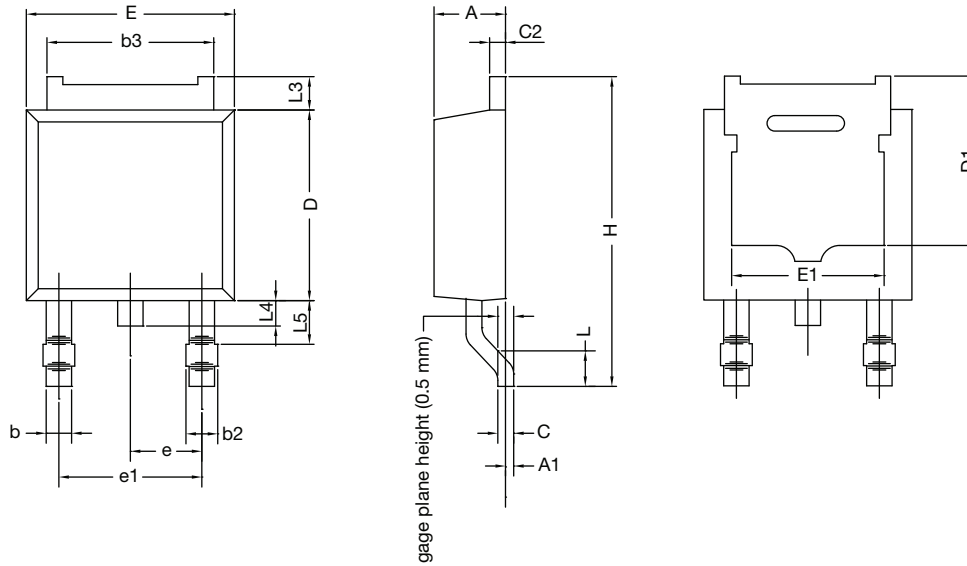
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction to Case ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65437.



TO-252AA Case Outline

VERSION 1: FACILITY CODE = Y



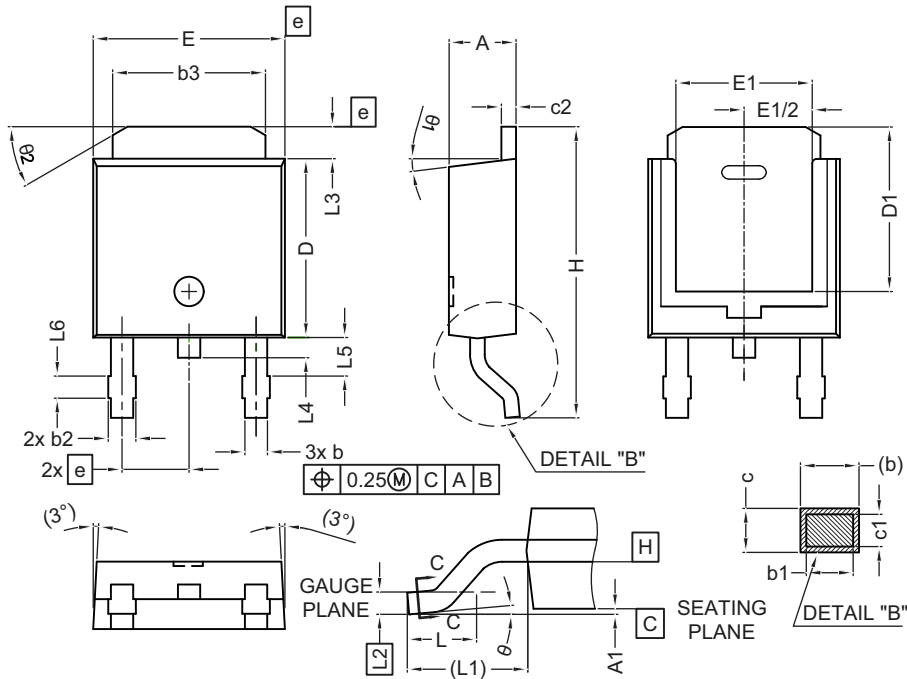
MILLIMETERS		
DIM.	MIN.	MAX.
A	2.18	2.38
A1	-	0.127
b	0.64	0.88
b2	0.76	1.14
b3	4.95	5.46
C	0.46	0.61
C2	0.46	0.89
D	5.97	6.22
D1	4.10	-
E	6.35	6.73
E1	4.32	-
H	9.40	10.41
e	2.28 BSC	
e1	4.56 BSC	
L	1.40	1.78
L3	0.89	1.27
L4	-	1.02
L5	1.01	1.52

Note

- Dimension L3 is for reference only



VERSION 2: FACILITY CODE = N



MILLIMETERS		
DIM.	MIN.	MAX.
A	2.18	2.39
A1	-	0.13
b	0.65	0.89
b1	0.64	0.79
b2	0.76	1.13
b3	4.95	5.46
c	0.46	0.61
c1	0.41	0.56
c2	0.46	0.60
D	5.97	6.22
D1	5.21	-
E	6.35	6.73
E1	4.32	-
e	2.29 BSC	
H	9.94	10.34

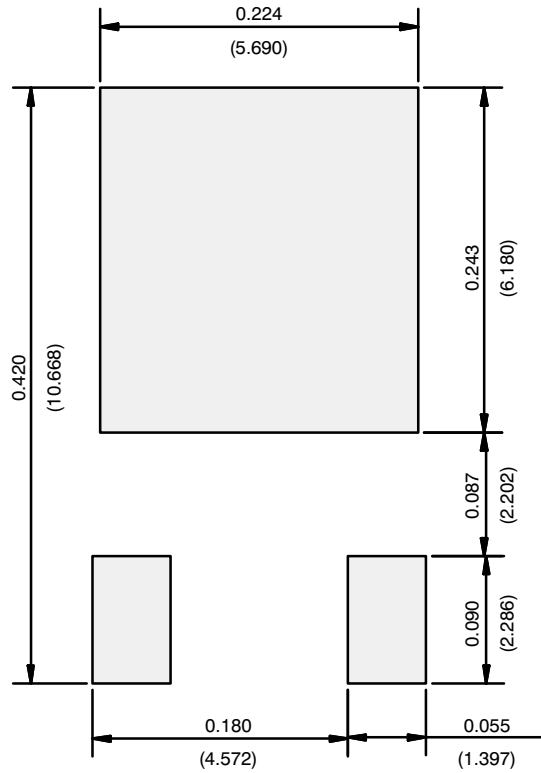
MILLIMETERS		
DIM.	MIN.	MAX.
L	1.50	1.78
L1	2.74 ref.	
L2	0.51 BSC	
L3	0.89	1.27
L4	-	1.02
L5	1.14	1.49
L6	0.65	0.85
θ	0°	10°
θ1	0°	15°
θ2	25°	35°

Notes

- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- Radius on terminal is optional

ECN: E19-0649-Rev. Q, 16-Dec-2019
 DWG: 5347

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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